









development

SN74AHCT02-Q1 JAJSQF5 - MAY 2023

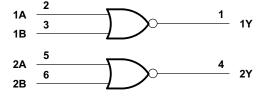
SN74AHCT02-Q1 車載用クワッド 2 入力正論理 NOR ゲート

1 特長

- 車載アプリケーション用に AEC-Q100 認定済み:
 - デバイス温度グレード 1:-40℃~+125℃
 - デバイス HBM ESD 分類レベル 2
 - デバイス CDM ESD 分類レベル C4B
- ウェッタブル・フランク QFN (WBQA) パッケージで供 給されます
- 動作範囲:4.5V~5.5V
- 低消費電力、I_{CC}の最大値 10μA
- 5V で ±8mA の出力駆動能力
- 入力は TTL 電圧互換
- JESD 17 準拠で 250mA 超のラッチアップ性能

2 アプリケーション

- デジタル信号のイネーブルまたはディスエーブル
- インジケータ LED の制御
- 通信モジュールとシステム・コントローラ間の変換



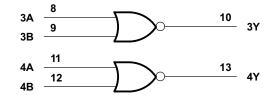
3 概要

これらのデバイスには 4 つの独立した 2 入力 NOR ゲー トが内蔵されており、ブール関数 $Y = \overline{A} \cdot \overline{B}$ または $Y = \overline{A + B}$ Bを正論理で実行します。

パッケージ情報

部品番号	パッケージ (1)	パッケージ・サイ ズ ⁽¹⁾	本体サイズ (公 称) ⁽¹⁾
	PW (SOP, 14)	5mm × 6.4mm	5mm × 4.4mm
SN74AHCT02	BQA (WQFN、 14)	3mm × 2.5mm	3mm × 2.5mm

利用可能なすべてのパッケージについては、このデータシートの 末尾にある注文情報を参照してください。



論理図 (正論理)



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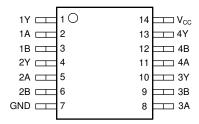
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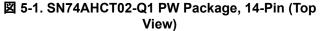
4 Revision History

資料番号末尾の英字は改訂を表しています。その改訂履歴は英語版に準じています。

DATE	REVISION	NOTES
May 2023	*	Initial Release

5 Pin Configuration and Functions





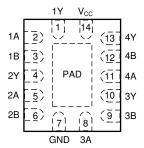


図 5-2. SN74AHCT02-Q1 BQA Package, 14-Pin (Top View)

表 5-1. Pin Functions

	PIN TYPE ⁽¹⁾		DESCRIPTION
NAME	No.	IIPE	DESCRIPTION
1A	2	I	1A Input
1B	3	I	1B Input
1Y	1	0	1Y Output
2A	5	I	2A Input
2B	6	I	2B Input
2Y	4	0	2Y Output
3A	8	I	3A Input
3B	9	I	3B Input
3Y	10	0	3Y Output
4A	11	1	4A Input
4B	12	I	4B Input
4Y	13	0	4Y Output
GND	7	G	Ground Pin
V _{CC}	14	Р	Power Pin
Thermal Pac	J (2)	-	The thermal pad can be connected to GND or left floating. Do not connect to any other signal or supply.

⁽¹⁾ I = input, O = output, I/O = input or output, G = ground, P = power.

⁽²⁾ BQA package only



6 Specifications

6.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted) (1)

			MIN	MAX	UNIT
V _{CC}	Supply voltage range		-0.5	7	V
V _I ⁽²⁾	Input voltage range	Input voltage range		7	V
V _O (2)	Output voltage range		-0.5	V _{CC} + 0.5	V
I _{IK}	Input clamp current	(V _I < 0)		-20	mA
Io	Output clamp current	(V _O < 0 or V _O > V _{CC)}		±20	mA
Io	Continuous output current	(V _O = 0 to V _{CC})		±25	mA
	Continuous current through V _{CC} or	GND		±50	mA
T _{stg}	Storage temperature range		-65	150	°C

⁽¹⁾ Stresses beyond those listed under Absolute Maximum Ratings may cause permanent damage to the device. These are stress ratings only, which do not imply functional operation of the device at these or any other conditions beyond those indicated under Recommended Operating Conditions. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

6.2 ESD Ratings

			VALUE	UNIT
V	V (ESD) Electrostatic discharge	Human body model (HBM), per AEC Q100-002 HBM ESD Classification Level 2 ⁽¹⁾	±2000	V
V _(ESD) Ele	D) Liectrostatic discriarge	Charged device model (CDM), per AEC Q100-011 CDM ESD Classification Level C4B	±1000	V

⁽¹⁾ AEC Q100-002 indicate that HBM stressing shall be in accordance with the ANSI/ESDA/JEDEC JS-001 specification.

6.3 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)(1)

		MIN	MAX	UNIT
V _{CC}	Supply voltage	4.5	5.5	V
V _{IH}	High-level input voltage	2		V
V _{IL}	Low-level input voltage		0.8	V
VI	Input voltage	0	5.5	V
Vo	Output voltage	0	V _{CC}	V
I _{OH}	High-level output current		-8	mA
I _{OL}	Low-level output current		8	mA
Δt/Δν	Input transition rise or fall rate		20	ns/V
T _A	Operating free-air temperature	-40	125	°C

⁽¹⁾ All unused inputs of the device must be held at V_{CC} or GND for proper device operation. Refer to the TI application report, Implications of Slow or Floating CMOS Inputs.

⁽²⁾ The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

6.4 Thermal Information

		SN74AH		
THERMAL METRIC ⁽¹⁾		BQA (WQFN)	PW (TSSOP)	UNIT
		14 PINS	14 PINS	
R _{0JA}	Junction-to-ambient thermal resistance	88.3	151.0	°C/W
R _{0JC(top)}	Junction-to-case (top) thermal resistance	90.9	80.0	°C/W
R _{0JB}	Junction-to-board thermal resistance	56.8	94.2	°C/W
Ψ_{JT}	Junction-to-top characterization parameter	9.9	28.0	°C/W
Y_{JB}	Junction-to-board characterization parameter	56.7	93.6	°C/W
R _{0JC(bot)}	Junction-to-case (bottom) thermal resistance	33.4	N/A	°C/W

⁽¹⁾ For more information about traditional and new thermal metrics, see the IC Package Thermal Metrics application report, SPRA953.

6.5 Electrical Characteristics

over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER	ETER TEST CONDITIONS		T _A = 25°C			T _A = -40°C t	UNIT	
PARAMETER	TEST CONDITIONS	VCC	MIN	TYP	MAX	MIN	MAX	UNII
V	I _{OH} = -50 μA	4.5 V	4.4	4.5		4.4		V
V _{OH}	I _{OH} = −8 mA	4.5 V	3.94			3.8		V
V	I _{OL} = 50 μA	4.5 V			0.1		0.1	V
V _{OL}	I _{OL} = 8 mA	4.5 V			0.36		0.44	V
I _I	V _I = 5.5 V or GND	0 V to 5.5 V			±0.1		±1	μA
I _{cc}	$V_I = V_{CC}$ or GND, $I_O = 0$	5.5 V			2		20	μA
	One input at 3.4 V,			,				
ΔI _{CC} ⁽¹⁾	Other inputs at GND or VCC	5.5 V			1.35		1.5	mA
Ci	VI = VCC or GND	5 V		4	10		10	pF

⁽¹⁾ This is the increase in supply current for each input at one of the specified TTL voltage levels, rather than 0 V or V_{CC}.

6.6 Switching Characteristics

over operating free-air temperature range, V_{CC} = 5 V \pm 0.5 V (unless otherwise noted). See Parameter Measurement Information

PARAMETER	FROM	то	LOAD	T	= 25°C		T _A = -40°C t	o 125°C	UNIT
(INPUT)	(OUTPUT) CAPACITANCE	MIN	TYP	MAX	MIN	MAX	ONII		
t _{PLH}	A or B Y	V	C = 15 pE		2.4	5.5	1	6.5	no
t _{PHL}		'	C _L = 15 pF		3.5	5.5	1	6.5	ns
t _{PLH}	- A or B	V	C = 50 pE		3.4	7.5	1	8.5	no
t _{PHL}		Ţ	C _L = 50 pF		4.5	7.5	1	8.5	ns

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6.7 Noise Characteristics

 V_{CC} = 5 V, C_L = 50 pF, T_A = 25°C (unless otherwise noted)⁽¹⁾

	PARAMETER			SN74AHCT02-Q1			
	PARAMETER	MIN	TYP	MAX	UNIT		
V _{OL(P)}	Quiet output, maximum dynamic V _{OL}			0.8	V		
V _{OL(V)}	Quiet output, minimum dynamic V _{OL}	-0.8			V		
V _{OH(V)}	Quiet output, minimum dynamic V _{OH}		4.7		V		
V _{IH(D})	High-level dynamic input voltage	2			V		
V _{IL(D)}	Low-level dynamic input voltage			0.8	V		

(1) Characteristics are for surface-mount packages only.

6.8 Operating Characteristics

 $V_{CC} = 5 \text{ V}, T_A = 25^{\circ}\text{C}$

PARAMETER		TEST CONDITIONS	TYP	UNIT
C _{pd}	Power dissipation capacitance1 2	No load, f = 1 MHz	17	pF

- 1. C_{PD} is used to determine the dynamic power consumption, per channel.
- 2. $P_D = V_{CC}^2 \times F_I \times (C_{PD} + C_L)$ where $F_I =$ input frequency, $C_L =$ output load capacitance, $V_{CC} =$ supply voltage.

6.9 Typical Characteristics

 $T_A = 25^{\circ}C$ (unless otherwise noted)

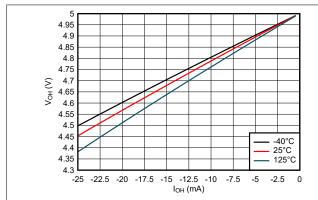


図 6-1. Output Voltage vs Current in HIGH State; 5-V Supply

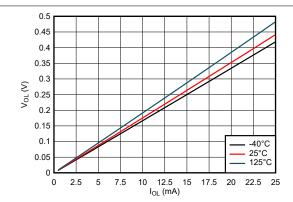
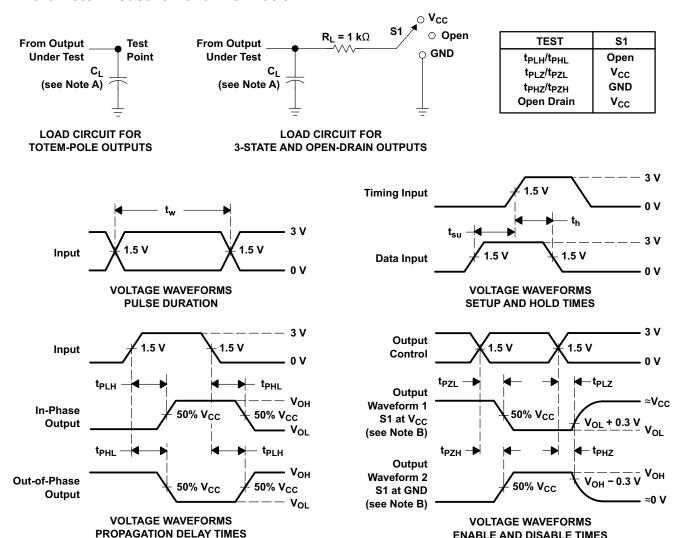


図 6-2. Output Voltage vs Current in LOW State; 5-V Supply



7 Parameter Measurement Information



NOTES: A. C_L includes probe and jig capacitance.

INVERTING AND NONINVERTING OUTPUTS

- B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
- C. All input pulses are supplied by generators having the following characteristics: PRR \leq 1 MHz, Z_O = 50 Ω , $t_f \leq$ 3 ns. $t_f \leq$ 3 ns.
- D. The outputs are measured one at a time with one input transition per measurement.
- E. All parameters and waveforms are not applicable to all devices.

図 7-1. Load Circuit and Voltage Waveforms

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ENABLE AND DISABLE TIMES

LOW- AND HIGH-LEVEL ENABLING

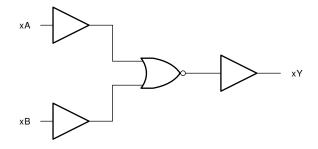


8 Detailed Description

8.1 Overview

This device contains four independent 2-input NOR Gates. Each gate performs the Boolean function $Y = \overline{A + B}$ in positive logic.

8.2 Functional Block Diagram



8.3 Feature Description

8.3.1 TTL-Compatible CMOS Inputs

This device includes TTL-compatible CMOS inputs. These inputs are specifically designed to interface with TTL logic devices by having a reduced input voltage threshold.

TTL-compatible CMOS inputs are high impedance and are typically modeled as a resistor in parallel with the input capacitance given in the *Electrical Characteristics*. The worst case resistance is calculated with the maximum input voltage, given in the *Absolute Maximum Ratings*, and the maximum input leakage current, given in the *Electrical Characteristics*, using Ohm's law $(R = V \div I)$.

TTL-compatible CMOS inputs require that input signals transition between valid logic states quickly, as defined by the input transition time or rate in the *Recommended Operating Conditions* table. Failing to meet this specification will result in excessive power consumption and could cause oscillations. More details can be found in the *Implications of Slow or Floating CMOS Inputs* application report.

Do not leave TTL-compatible CMOS inputs floating at any time during operation. Unused inputs must be terminated at V_{CC} or GND. If a system will not be actively driving an input at all times, a pull-up or pull-down resistor can be added to provide a valid input voltage during these times. The resistor value will depend on multiple factors; however, a 10-k Ω resistor is recommended and will typically meet all requirements.

8.3.2 Balanced CMOS Push-Pull Outputs

This device includes balanced CMOS push-pull outputs. The term *balanced* indicates that the device can sink and source similar currents. The drive capability of this device may create fast edges into light loads, so routing and load conditions should be considered to prevent ringing. Additionally, the outputs of this device are capable of driving larger currents than the device can sustain without being damaged. It is important for the output power of the device to be limited to avoid damage due to overcurrent. The electrical and thermal limits defined in the *Absolute Maximum Ratings* must be followed at all times.

Unused push-pull CMOS outputs should be left disconnected.

8.3.3 Clamp Diode Structure

As \boxtimes 8-1 shows, the outputs to this device have both positive and negative clamping diodes, and the inputs to this device have negative clamping diodes only.

注意

Voltages beyond the values specified in the *Absolute Maximum Ratings* table can cause damage to the device. The input and output voltage ratings may be exceeded if the input and output clamp-current ratings are observed.

Product Folder Links: SN74AHCT02-Q1

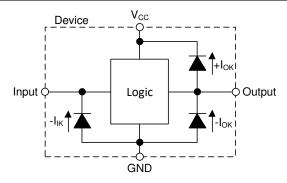


図 8-1. Electrical Placement of Clamping Diodes for Each Input and Output

8.3.4 Wettable Flanks

This device includes wettable flanks for at least one package. See the *Features* section on the front page of the data sheet for which packages include this feature.

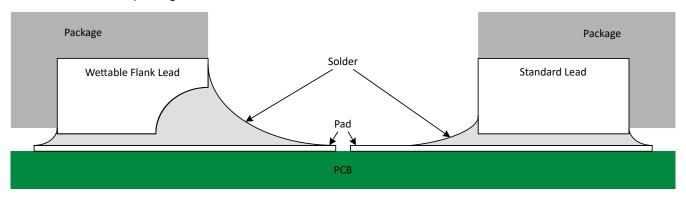


図 8-2. Simplified Cutaway View of Wettable-Flank QFN Package and Standard QFN Package After Soldering

Wettable flanks help improve side wetting after soldering, which makes QFN packages easier to inspect with automatic optical inspection (AOI). As shown in 🗵 8-2, a wettable flank can be dimpled or step-cut to provide additional surface area for solder adhesion which assists in reliably creating a side fillet. See the mechanical drawing for additional details.

8.4 Device Functional Modes

表 8-1. Function Table

INF	OUTPUT			
Α	В	Y		
Н	Х	L		
Х	Н	L		
L	L	Н		

(1) H = High Voltage Level, L = Low Voltage Level, X = Don't Care

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9 Application and Implementation

注

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes, as well as validating and testing their design implementation to confirm system functionality.

9.1 Application Information

In this application, two 2-input NOR gates are used to create an SR latch as shown in Typical application block diagram. The two additional gates can be used for a second SR latch, or the inputs can be grounded and both channels left unused.

The SN74AHCT02-Q1 is used to drive the tamper indicator LED and provide one bit of data to the system controller. When the tamper switch outputs HIGH, the output Q becomes HIGH. This output remains HIGH until the system controller addresses the event and sends a HIGH signal to the R input which returns the Q output back to LOW.

The user can add a small RC to the feedback path of the NOR gates to default the output to a certain state, which can create slow transition rates. This fact makes the SN74AHCT02-Q1 ideal for the application because it has Schmitt-trigger inputs that do not have input transition rate requirements.

9.2 Typical Application

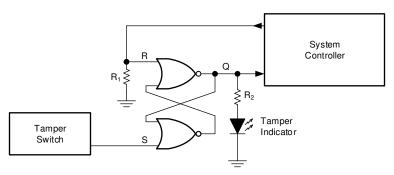


図 9-1. Typical application block diagram

9.2.1 Design Requirements

9.2.1.1 Power Considerations

Ensure the desired supply voltage is within the range specified in the *Recommended Operating Conditions*. The supply voltage sets the device's electrical characteristics as described in the *Electrical Characteristics* section.

The positive voltage supply must be capable of sourcing current equal to the maximum static supply current, I_{CC}, listed in the *Electrical Characteristics*, and any transient current required for switching.

The ground must be capable of sinking current equal to the total current to be sunk by all outputs of the SN74AHCT02-Q1 plus the maximum supply current, I_{CC}, listed in the *Electrical Characteristics*, and any transient current required for switching. The logic device can only sink as much current that can be sunk into its ground connection. Be sure to not exceed the maximum total current through GND listed in the *Absolute Maximum Ratings*.

The SN74AHCT02-Q1 can drive a load with a total capacitance less than or equal to 50 pF while still meeting all of the data sheet specifications. Larger capacitive loads can be applied; however, it is not recommended to exceed 50 pF.

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The SN74AHCT02-Q1 can drive a load with total resistance described by $R_L \ge V_O / I_O$, with the output voltage and current defined in the *Electrical Characteristics* table with V_{OL} . When outputting in the HIGH state, the output voltage in the equation is defined as the difference between the measured output voltage and the supply voltage at the V_{CC} pin.

Total power consumption can be calculated using the information provided in *CMOS Power Consumption and Cpd Calculation*.

Thermal increase can be calculated using the information provided in *Thermal Characteristics of Standard Linear* and Logic (SLL) Packages and Devices.

注意

The maximum junction temperature, $T_{J(max)}$ listed in the *Absolute Maximum Ratings*, is an additional limitation to prevent damage to the device. Do not violate any values listed in the *Absolute Maximum Ratings*. These limits are provided to prevent damage to the device.

9.2.1.2 Input Considerations

Input signals must cross to be considered a logic LOW, and to be considered a logic HIGH. Do not exceed the maximum input voltage range found in the *Absolute Maximum Ratings*.

Unused inputs must be terminated to either V_{CC} or ground. The unused inputs can be directly terminated if the input is completely unused, or they can be connected with a pull-up or pull-down resistor if the input will be used sometimes, but not always. A pull-up resistor is used for a default state of HIGH, and a pull-down resistor is used for a default state of LOW. The drive current of the controller, leakage current into the SN74AHCT02-Q1 (as specified in the *Electrical Characteristics*), and the desired input transition rate limits the resistor size. A 10-k Ω resistor value is often used due to these factors.

Refer to the Feature Description section for additional information regarding the inputs for this device.

9.2.1.3 Output Considerations

The ground voltage is used to produce the output LOW voltage. Sinking current into the output will increase the output voltage as specified by the V_{OL} specification in the *Electrical Characteristics*.

Unused outputs can be left floating. Do not connect outputs directly to V_{CC} or ground.

Refer to the Feature Description section for additional information regarding the outputs for this device.

9.2.2 Detailed Design Procedure

- Add a decoupling capacitor from V_{CC} to GND. The capacitor needs to be placed physically close to the device and electrically close to both the V_{CC} and GND pins. An example layout is shown in the *Layout* section.
- 2. Ensure the capacitive load at the output is ≤ 50 pF. This is not a hard limit; by design, however, it will optimize performance. This can be accomplished by providing short, appropriately sized traces from the SN74AHCT02-Q1 to one or more of the receiving devices.
- 3. Ensure the resistive load at the output is larger than $(V_{CC} / I_{O(max)}) \Omega$. Doing this will prevent the maximum output current from the *Absolute Maximum Ratings* from being violated. Most CMOS inputs have a resistive load measured in M Ω ; much larger than the minimum calculated previously.
- 4. Thermal issues are rarely a concern for logic gates; the power consumption and thermal increase, however, can be calculated using the steps provided in the application report, *CMOS Power Consumption and Cpd Calculation*.

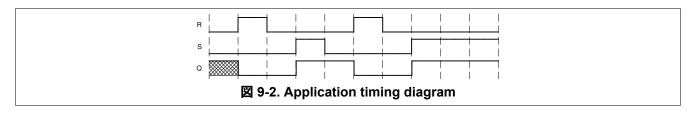
Product Folder Links: SN74AHCT02-Q1

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9.2.3 Application Curves



9.3 Power Supply Recommendations

The power supply can be any voltage between the minimum and maximum supply voltage rating located in the *Recommended Operating Conditions*. Each V_{CC} terminal should have a good bypass capacitor to prevent power disturbance. A 0.1- μ F capacitor is recommended for this device. It is acceptable to parallel multiple bypass caps to reject different frequencies of noise. The 0.1- μ F and 1- μ F capacitors are commonly used in parallel. The bypass capacitor should be installed as close to the power terminal as possible for best results, as shown in given example layout image.

9.4 Layout

9.4.1 Layout Guidelines

When using multiple-input and multiple-channel logic devices inputs must not ever be left floating. In many cases, functions or parts of functions of digital logic devices are unused; for example, when only two inputs of a triple-input AND gate are used or only 3 of the 4 buffer gates are used. Such unused input pins must not be left unconnected because the undefined voltages at the outside connections result in undefined operational states. All unused inputs of digital logic devices must be connected to a logic high or logic low voltage, as defined by the input voltage specifications, to prevent them from floating. The logic level that must be applied to any particular unused input depends on the function of the device. Generally, the inputs are tied to GND or V_{CC}, whichever makes more sense for the logic function or is more convenient.

9.4.2 Layout Example

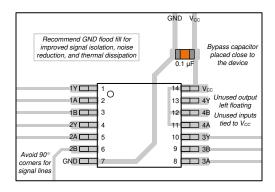


図 9-3. Example layout for the SN74AHCT02-Q1

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10 Device and Documentation Support

10.1 ドキュメントの更新通知を受け取る方法

ドキュメントの更新についての通知を受け取るには、ti.com のデバイス製品フォルダを開いてください。「更新の通知を受け取る」をクリックして登録すると、変更されたすべての製品情報に関するダイジェストを毎週受け取れます。変更の詳細については、修正されたドキュメントに含まれている改訂履歴をご覧ください。

10.2 サポート・リソース

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10.4 静電気放電に関する注意事項



この IC は、ESD によって破損する可能性があります。テキサス・インスツルメンツは、IC を取り扱う際には常に適切な注意を払うことを推奨します。正しい取り扱いおよび設置手順に従わない場合、デバイスを破損するおそれがあります。

ESD による破損は、わずかな性能低下からデバイスの完全な故障まで多岐にわたります。精密な IC の場合、パラメータがわずかに変化するだけで公表されている仕様から外れる可能性があるため、破損が発生しやすくなっています。

10.5 用語集

テキサス・インスツルメンツ用語集 この用語集には、用語や略語の一覧および定義が記載されています。

11 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

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PACKAGING INFORMATION

Orderable part number	Status	Material type	Package Pins	Package qty Carrier	RoHS	Lead finish/ Ball material	MSL rating/ Peak reflow	Op temp (°C)	Part marking
	(1)	(2)			(3)	(4)	(5)		(6)
SN74AHCT02QPWRQ1	Active	Production	TSSOP (PW) 14	3000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	LVT02Q
SN74AHCT02QPWRQ1.A	Active	Production	TSSOP (PW) 14	3000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	LVT02Q
SN74AHCT02QWBQARQ1	Active	Production	WQFN (BQA) 14	3000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	AHT02Q
SN74AHCT02QWBQARQ1.A	Active	Production	WQFN (BQA) 14	3000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	AHT02Q

⁽¹⁾ Status: For more details on status, see our product life cycle.

Multiple part markings will be inside parentheses. Only one part marking contained in parentheses and separated by a "~" will appear on a part. If a line is indented then it is a continuation of the previous line and the two combined represent the entire part marking for that device.

Important Information and Disclaimer: The information provided on this page represents TI's knowledge and belief as of the date that it is provided. TI bases its knowledge and belief on information provided by third parties, and makes no representation or warranty as to the accuracy of such information. Efforts are underway to better integrate information from third parties. TI has taken and continues to take reasonable steps to provide representative and accurate information but may not have conducted destructive testing or chemical analysis on incoming materials and chemicals. TI and TI suppliers consider certain information to be proprietary, and thus CAS numbers and other limited information may not be available for release.

In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

OTHER QUALIFIED VERSIONS OF SN74AHCT02-Q1:

⁽²⁾ Material type: When designated, preproduction parts are prototypes/experimental devices, and are not yet approved or released for full production. Testing and final process, including without limitation quality assurance, reliability performance testing, and/or process qualification, may not yet be complete, and this item is subject to further changes or possible discontinuation. If available for ordering, purchases will be subject to an additional waiver at checkout, and are intended for early internal evaluation purposes only. These items are sold without warranties of any kind.

⁽³⁾ RoHS values: Yes, No, RoHS Exempt. See the TI RoHS Statement for additional information and value definition.

⁽⁴⁾ Lead finish/Ball material: Parts may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

⁽⁵⁾ MSL rating/Peak reflow: The moisture sensitivity level ratings and peak solder (reflow) temperatures. In the event that a part has multiple moisture sensitivity ratings, only the lowest level per JEDEC standards is shown. Refer to the shipping label for the actual reflow temperature that will be used to mount the part to the printed circuit board.

⁽⁶⁾ Part marking: There may be an additional marking, which relates to the logo, the lot trace code information, or the environmental category of the part.

PACKAGE OPTION ADDENDUM

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● Catalog : SN74AHCT02

Military : SN54AHCT02

NOTE: Qualified Version Definitions:

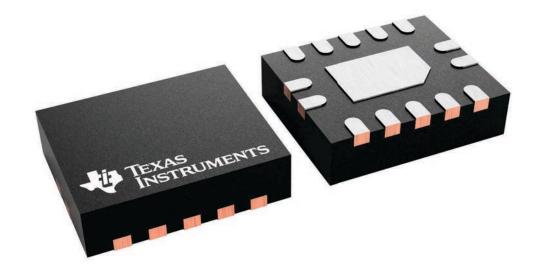
Catalog - TI's standard catalog product

• Military - QML certified for Military and Defense Applications

2.5 x 3, 0.5 mm pitch

PLASTIC QUAD FLATPACK - NO LEAD

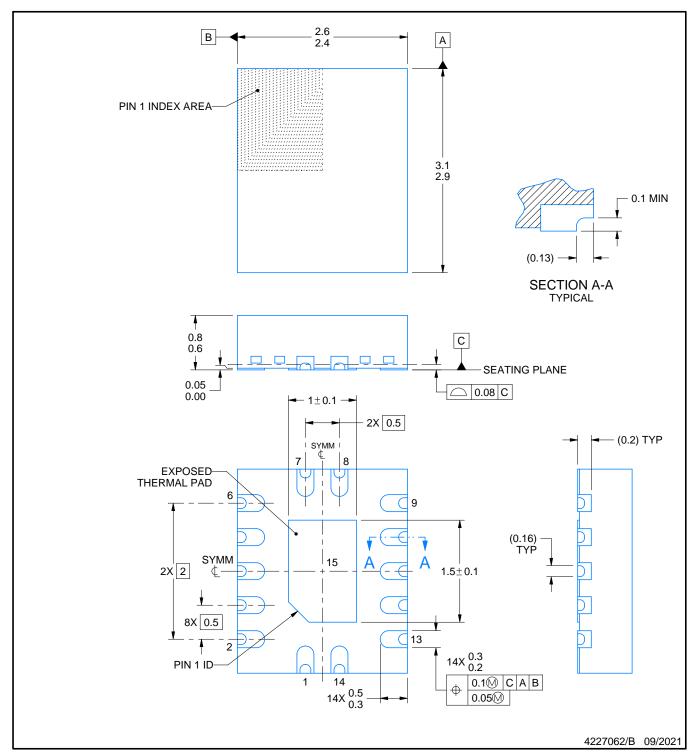
This image is a representation of the package family, actual package may vary. Refer to the product data sheet for package details.



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PLASTIC QUAD FLATPACK - NO LEAD

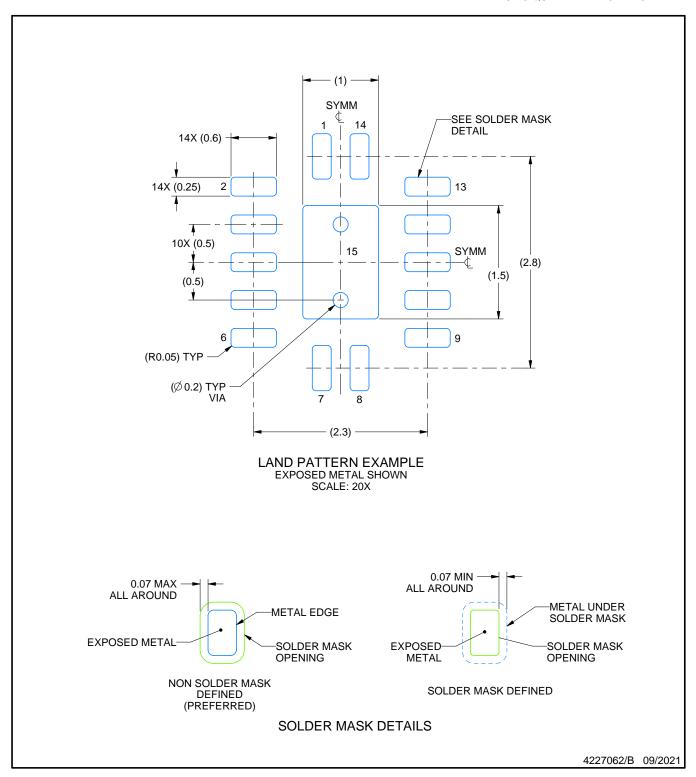


NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
 2. This drawing is subject to change without notice.
- 3. The package thermal pad must be soldered to the printed circuit board for thermal and mechanical performance.



PLASTIC QUAD FLATPACK - NO LEAD

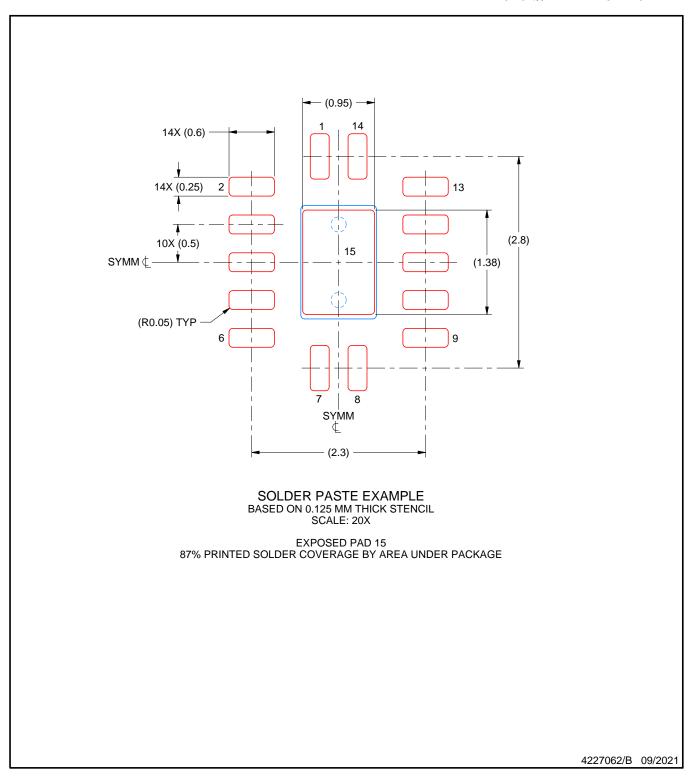


NOTES: (continued)

- 4. This package is designed to be soldered to a thermal pad on the board. For more information, see Texas Instruments literature number SLUA271 (www.ti.com/lit/slua271).
- 5. Vias are optional depending on application, refer to device data sheet. If any vias are implemented, refer to their locations shown on this view. It is recommended that vias under paste be filled, plugged or tented.



PLASTIC QUAD FLATPACK - NO LEAD



NOTES: (continued)

^{6.} Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.





SMALL OUTLINE PACKAGE



NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.

 2. This drawing is subject to change without notice.

 3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not
- exceed 0.15 mm per side.
- 4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.25 mm per side.
- 5. Reference JEDEC registration MO-153.



SMALL OUTLINE PACKAGE



NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



SMALL OUTLINE PACKAGE



NOTES: (continued)

- 8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 9. Board assembly site may have different recommendations for stencil design.



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